



SEMITOP®E1

## IGBT module

### Engineering Sample

### SK35GD12T4ETE1

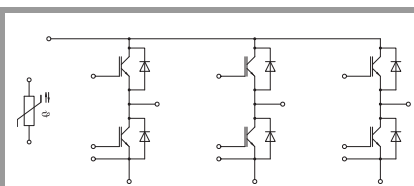
#### Target Data

#### Features

- Low inductive design
- Press-Fit contact technology
- Rugged mounting due to integrated mounting clamps
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
- 1200V Trench4 IGBT technology
- CAL4F diode technology
- UL recognized file no. E 63 532
- Integrated NTC temperature sensor

#### Typical Applications\*

- Inverter up to 33kVA
- Typical motor power 15kW



GD-ET

#### Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
<b>Inverter - IGBT</b>			
$V_{CES}$	$T_j = 25\text{ °C}$	1200	V
$I_C$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	43
		$T_s = 70\text{ °C}$	35
$I_{Cnom}$		35	A
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	105	A
$V_{GES}$		-20 ... 20	V
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150\text{ °C}$	10
$T_j$		-40 ... 175	°C
<b>Inverse - Diode</b>			
$V_{RRM}$	$T_j = 25\text{ °C}$	1200	V
$I_F$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	38
		$T_s = 70\text{ °C}$	30
$I_{Fnom}$		35	A
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	105	A
$I_{FSM}$	10 ms, sin 180°, $T_j = 150\text{ °C}$	170	A
$T_j$		-40 ... 175	°C
<b>Module</b>			
$I_{t(RMS)}$	$T_{terminal} = 100\text{ °C}$ , $T_s = 60\text{ °C}$ , per pin	t.b.d.	A
$T_{stg}$		-40 ... 125	°C
$V_{isol}$	AC, sinusoidal, $t = 1\text{ min}$	2500	V

#### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>Inverter - IGBT</b>					
$V_{CE(sat)}$	$I_C = 35\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	1.85	2.10	V
		$T_j = 150\text{ °C}$	2.25	2.45	V
$V_{CE0}$	chipelevel	$T_j = 25\text{ °C}$	0.80	0.90	V
		$T_j = 150\text{ °C}$	0.70	0.80	V
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25\text{ °C}$	30	34	mΩ
		$T_j = 150\text{ °C}$	44	47	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 1.2\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = 1200\text{ V}$ , $T_j = 25\text{ °C}$			0.06	mA
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	1.95		nF
$C_{oes}$		$f = 1\text{ MHz}$	0.155		nF
$C_{res}$		$f = 1\text{ MHz}$	0.115		nF
$Q_G$	- 8 V...+ 15 V		270		nC
$R_{Gint}$	$T_j = 25\text{ °C}$		0		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150\text{ °C}$	-		ns
$t_r$	$I_C = 35\text{ A}$	$T_j = 150\text{ °C}$	-		ns
$E_{on}$	$R_{G on} = 12\text{ Ω}$	$T_j = 150\text{ °C}$	3.15		mJ
$t_{d(off)}$	$R_{G off} = 12\text{ Ω}$	$T_j = 150\text{ °C}$	-		ns
$t_f$		$T_j = 150\text{ °C}$	-		ns
$E_{off}$	$V_{GE} = +15/-7\text{ V}$	$T_j = 150\text{ °C}$	3.2		mJ
$R_{th(j-s)}$	per IGBT		1.2		K/W



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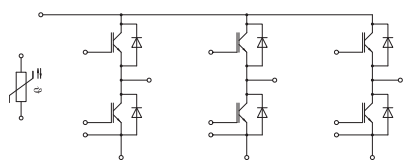
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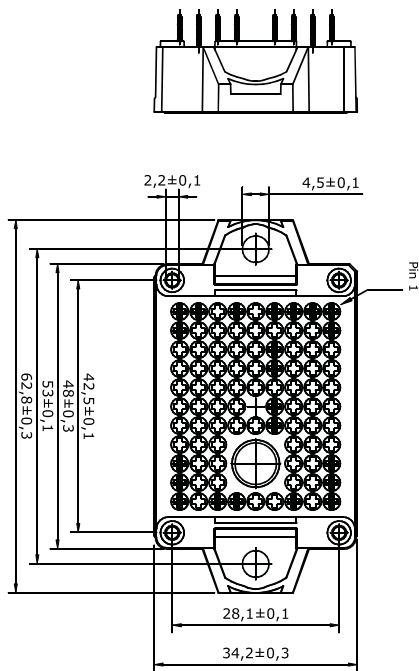
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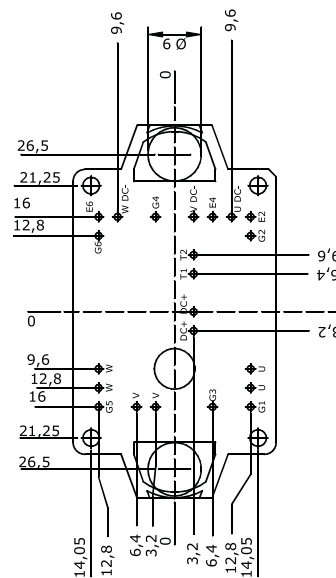
Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 35 A	T <sub>j</sub> = 25 °C		2.30	2.62	V
	chiplevel	T <sub>j</sub> = 150 °C		2.29	2.62	V
V <sub>F0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V
		T <sub>j</sub> = 150 °C		0.90	1.10	V
r <sub>F</sub>	chiplevel	T <sub>j</sub> = 25 °C		29	32	mΩ
		T <sub>j</sub> = 150 °C		40	43	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 35 A	T <sub>j</sub> = 150 °C		-		A
Q <sub>rr</sub>	V <sub>GE</sub> = -7 V	T <sub>j</sub> = 150 °C		-		μC
E <sub>rr</sub>	V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		2.6		mJ
R <sub>th(j-s)</sub>	per Diode			1.55		K/W
Module						
L <sub>CE</sub>				t.b.d.		nH
M <sub>s</sub>	to heatsink		2		2.1	Nm
w				24		g
Temperature Sensor						
R <sub>100</sub>	T <sub>c</sub> =100°C (R <sub>25</sub> =5 kΩ)			493 ± 5%		Ω
B <sub>100/125</sub>	R <sub>(T)</sub> =R <sub>100</sub> exp[B <sub>100/125</sub> (1/T-1/T <sub>100</sub> )]; T[K];			3550 ±2%		K



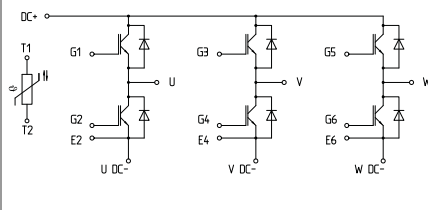
GD-ET



- Pin-Grid 3.2 mm
- Tolerance of PCB hole pattern  $\pm 0.025$
- Diameters of drill  $\varnothing 1.15\text{mm}$
- Copper thickness in hole 25 - 50  $\mu\text{m}$
- Hole specification for contacts: refer to SEMITOP E1, E2 mounting instruction



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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